

Electrical Characteristics at T_j
Static Characteristics

| Parameter | Symbol | Conditions | Value | | | Unit |
|-----------------------------------|---------------|------------------------------------|-------|-----|-----|------|
| | | | min | typ | max | |
| Drain to Source Breakdown Voltage | $V_{(BR)DSS}$ | $V_{GS}=0V, I_D=250mA$ | 200 | - | - | V |
| Gate Threshold Voltage | $V_{GS(th)}$ | $V_{GS}=V_{DS}, I_D=250mA$ | 2 | 3 | 4 | |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{GS}=0V, V_{DS}=160V, T_j$ | - | - | 1 | mA |
| | | $V_{GS}=0V, V_{DS}=160V, T_j$ | - | - | 100 | |
| Gate to Source Leakage Current | I_{GSS} | $V_{GS} = V_{DS}=0V$ | - | - | 100 | nA |
| Drain to Source on Resistance | $R_{DS(on)}$ | $V_{GS}=10V, I_D=20A$ | - | 4.7 | 5.6 | mW |
| Transconductance | g_{fs} | $V_{DS}=5V, I_D=20A$ | - | 90 | - | S |
| Gate Resistance | R_G | $V_{GS}=0V, V_{DS}$ Open, $f=1MHz$ | - | 2.0 | - | W |

Dynamic Characteristics

| | | | | | | |
|-------------------------------|--------------|--|---|------|---|----|
| Input Capacitance | C_{iss} | $V_{GS}=0V, V_{DS}=100V, f=1MHz$ | - | 9940 | - | pF |
| Output Capacitance | C_{oss} | | - | 840 | - | |
| Reverse Transfer Capacitance | C_{rss} | | - | 15 | - | |
| Total Gate Charge | Q_g | $V_{DD}=100V, I_D=20A, V_{GS}=10V$ | - | 112 | - | nC |
| Gate to Source Charge | Q_{gs} | | - | 36 | - | |
| Gate to Drain (Miller) Charge | Q_{gd} | | - | 10 | - | |
| Turn on Delay Time | $t_{d(on)}$ | $V_{DD}=100V, I_D=20A, V_{GS}=10V, R_G=10W,$ | - | 32 | - | ns |
| Rise time | t_r | | - | 44 | - | |
| Turn off Delay Time | $t_{d(off)}$ | | - | 76 | - | |
| Fall Time | t_f | | - | 20 | - | |

Reverse Diode Characteristics

| | | | | | | |
|-------------------------|----------|--------------------------------------|---|------|---|----|
| Diode Forward Voltage | V_{SD} | $V_{GS}=0V, I_F=20A$ | - | 0.9 | - | V |
| Reverse Recovery Time | t_{rr} | $V_R=100V, I_F=20A, di_F/dt=100A/ms$ | - | 280 | - | ns |
| Reverse Recovery Charge | Q_{rr} | | - | 1260 | - | nC |

Fig 1. Typical Output Characteristics

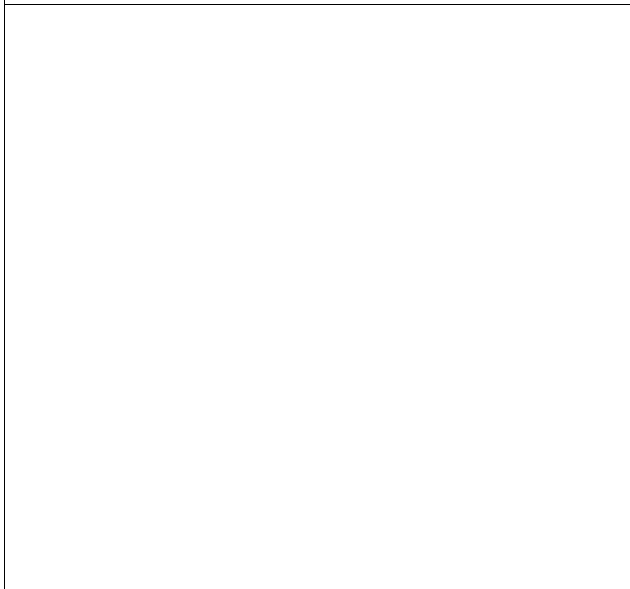


Figure 2. On-Resistance vs. Gate-Source Voltage

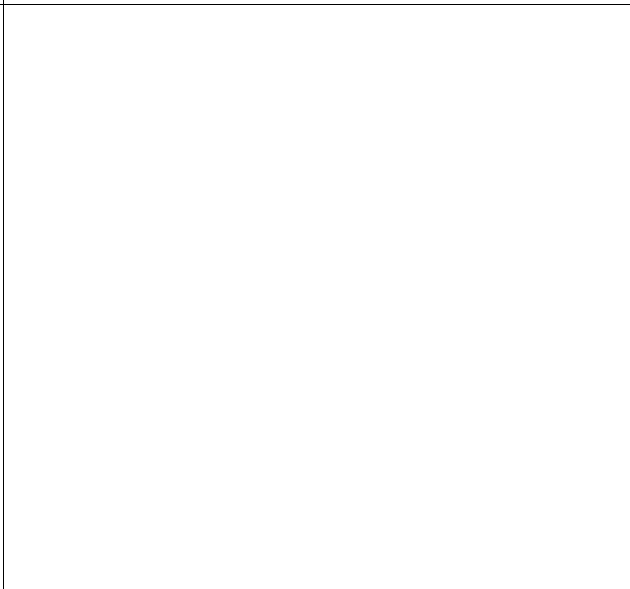


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

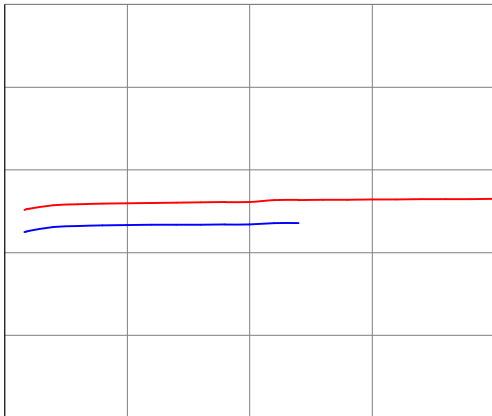


Figure 4. Normalized On-Resistance vs. Junction Temperature

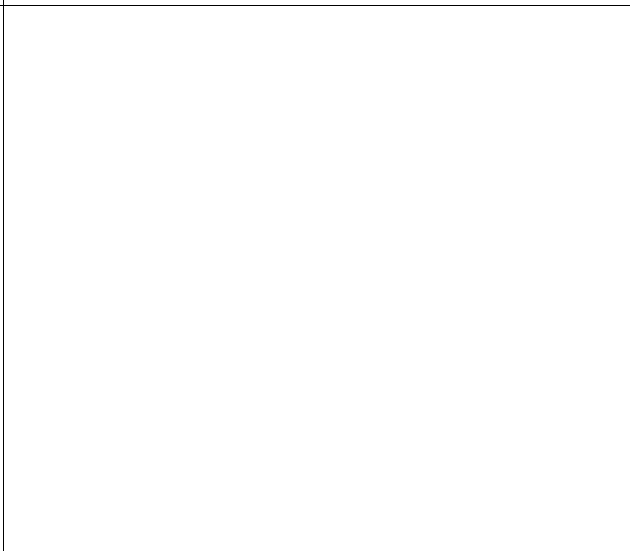


Figure 5. Typical Transfer Characteristics

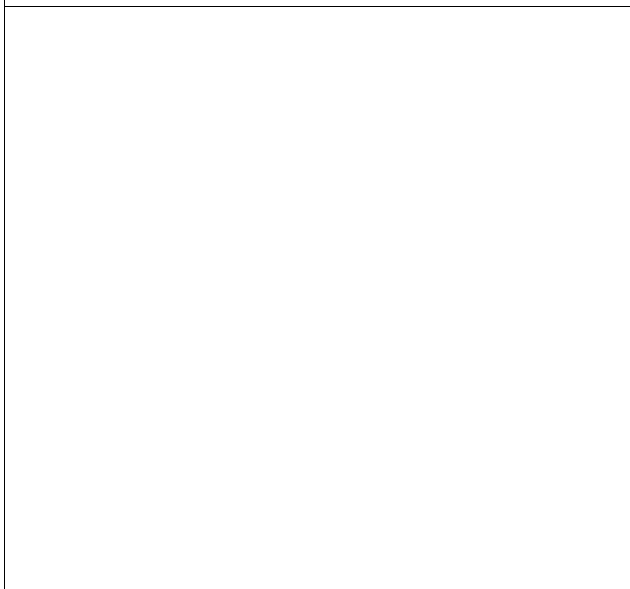


Figure 6. Typical Source-Drain Diode Forward Voltage

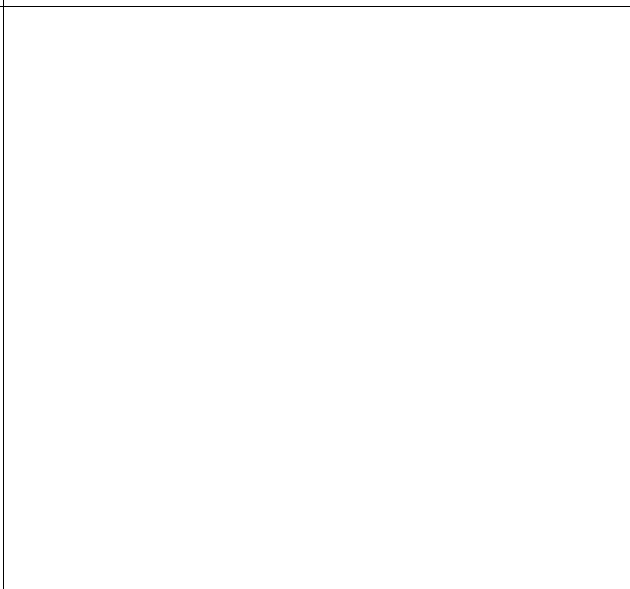


Figure 7. Typical Gate-Charge vs. Gate-to-Source Voltage

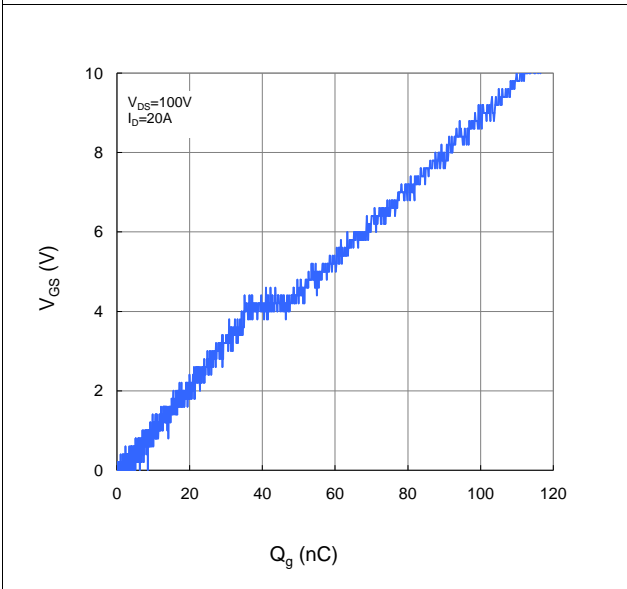


Figure 8. Typical Capacitance vs. Drain-to-Source Voltage

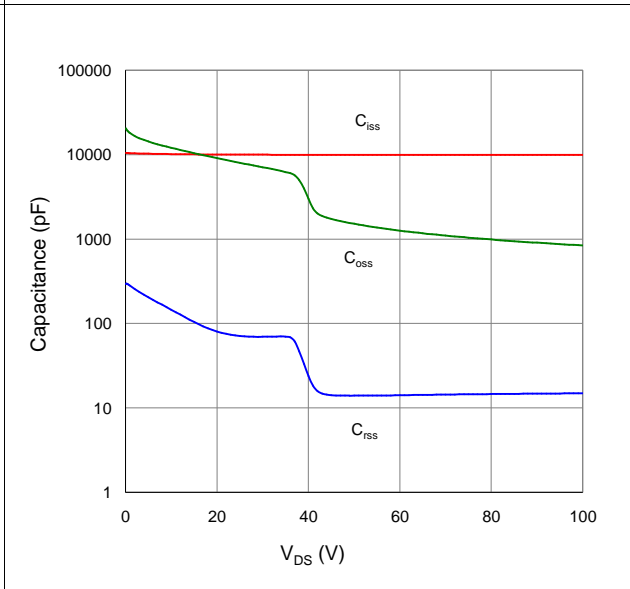


Figure 9. Maximum Safe Operating Area

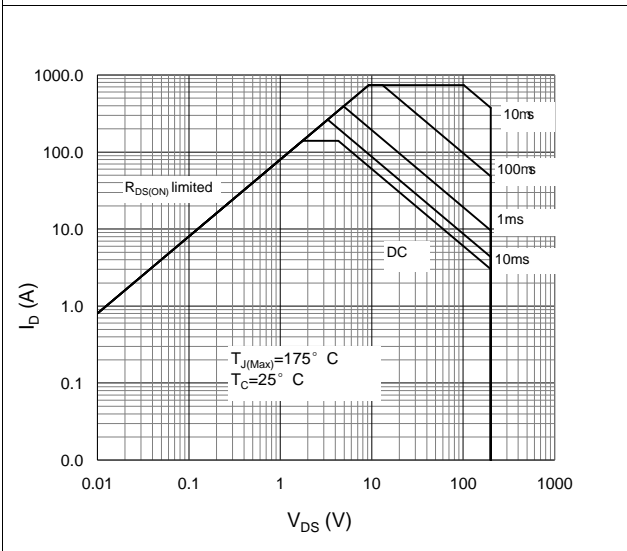


Figure 10. Maximum Drain Current vs. Case Temperature

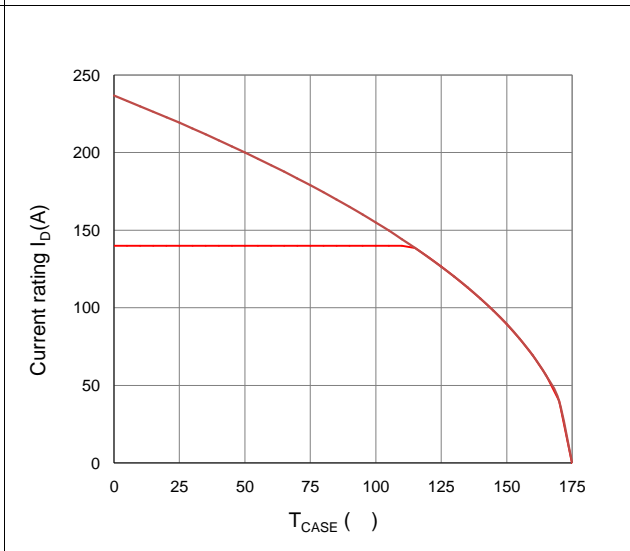
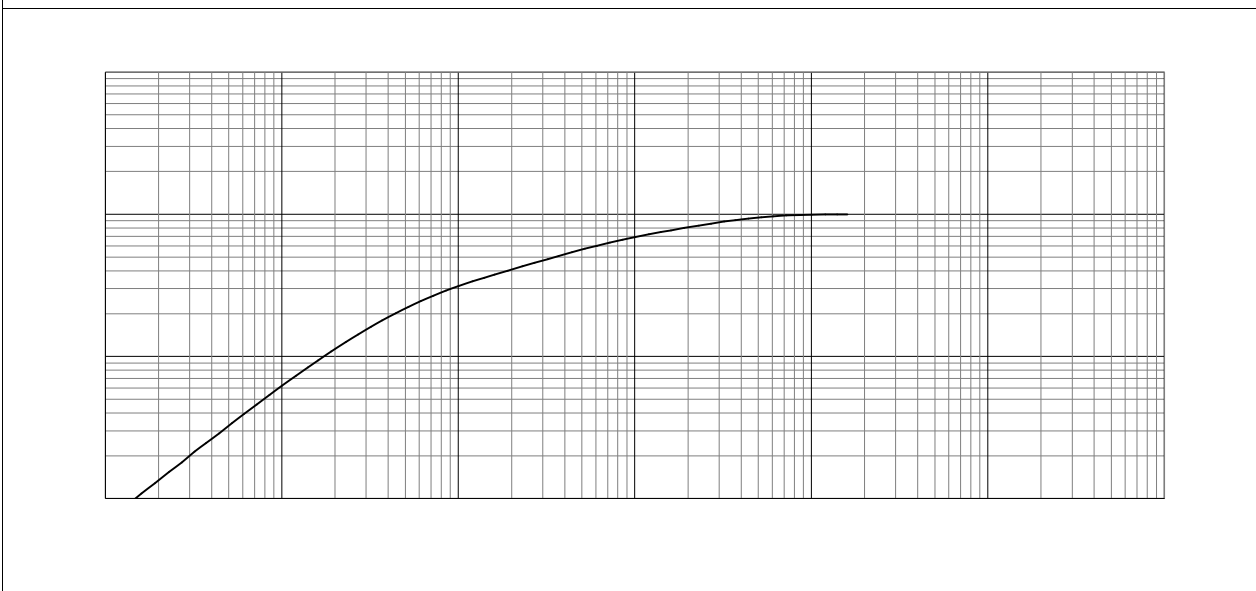
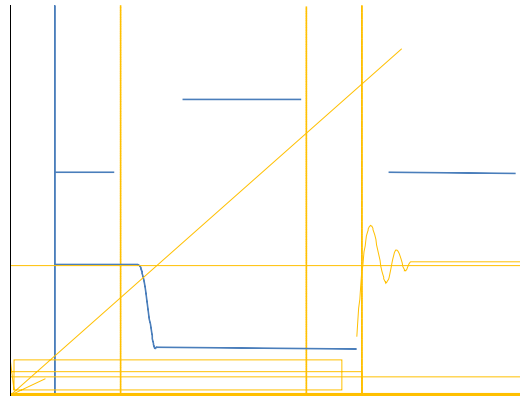


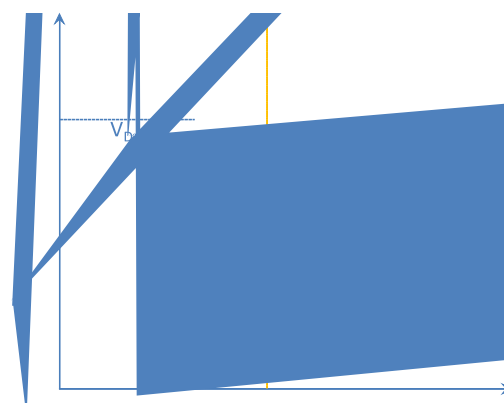
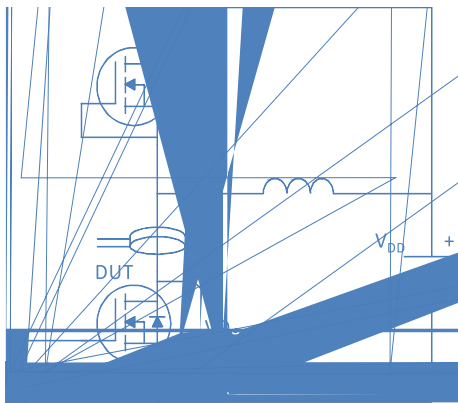
Figure 11. Normalized Maximum Transient Thermal Impedance, Junction-to-Case



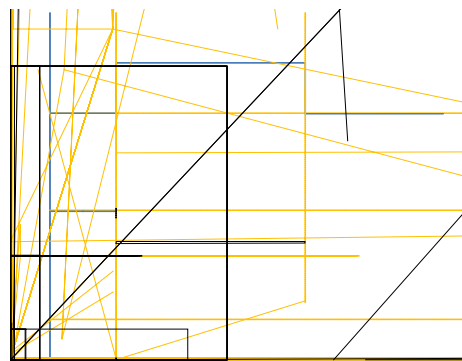
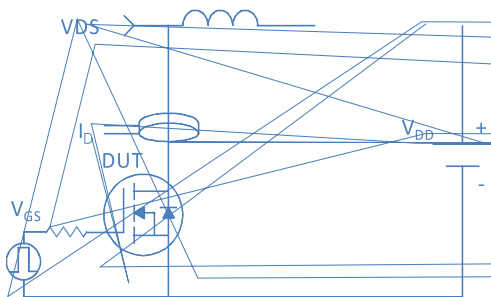
Inductive switching Test



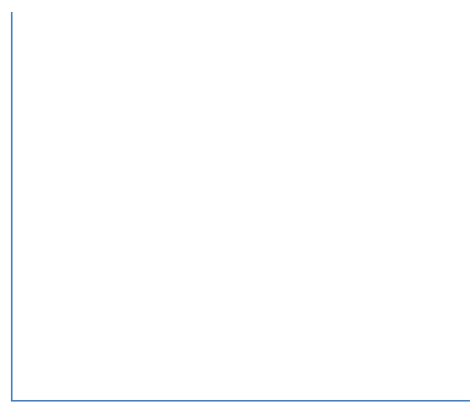
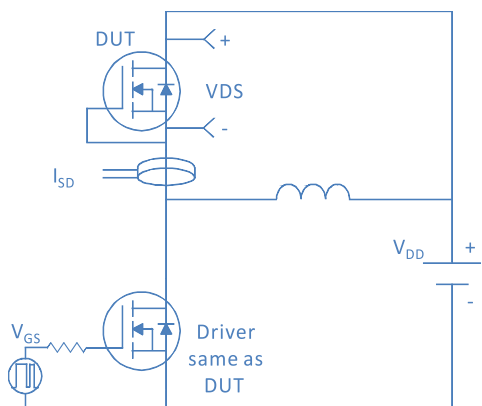
Gate Charge Test



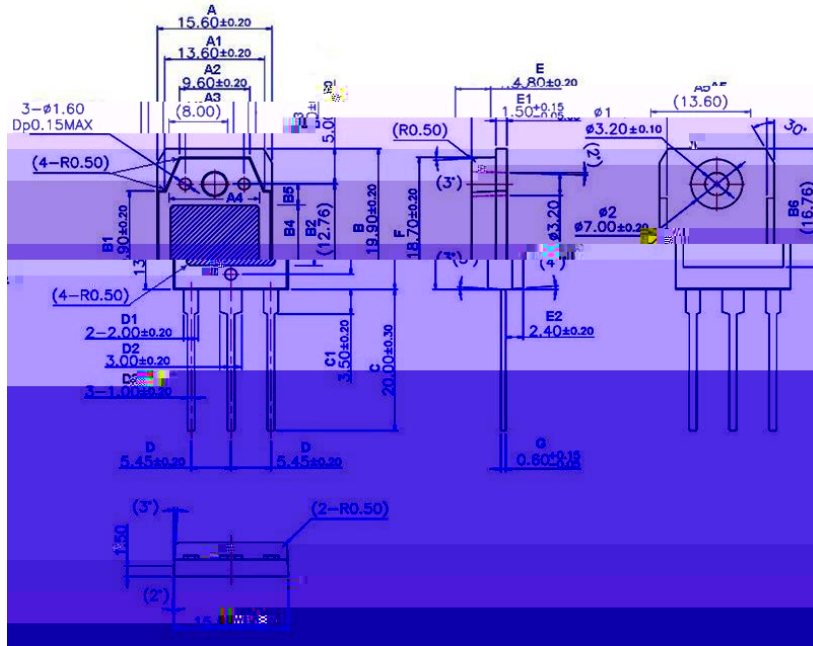
Uclamped Inductive Switching (UIS) Test



Diode Recovery Test



TO-3P, 3 leads



(单位: mm)

| 符号 | 尺寸 | 符号 | 尺寸 | 符号 | 尺寸 | 符号 | 尺寸 | | | | |
|------|-------|-------|----|---------|-------|---------|-------|-------|----|------|------|
| A | 15.40 | 15.80 | B1 | 13.70 | 14.10 | C1 | 3.30 | 3.70 | E2 | 2.20 | 2.60 |
| A2 | 9.40 | 9.80 | B3 | 4.80 | 5.20 | D1 | 1.80 | 2.20 | G | 0.50 | 0.90 |
| Φ2 | 6.80 | 7.20 | A4 | (12.00) | B5 | (3.00) | D3 | 0.80 | | | |
| 4.60 | 5.00 | | A5 | (13.60) | B6 | (16.76) | E | | | | |
| 1.45 | 1.65 | | B | 19.70 | 20.10 | C | 19.70 | 20.30 | F1 | | |